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11, 11606Joint experimental and theoretical study of
PbGa₂S₄ under compression†Tania Garcia-Sanchez,^a Samuel Gallego-Parra,^b Akun Liang,^c José Luis Rodrigo-Ramon,^c Alfonso Muñoz,^d Plácida Rodríguez-Hernandez,^d Javier Gonzalez-Platas,^d Juan Ángel Sans,^b Vanesa Paula Cuenca-Gotor,^b Hussien H. Osman,^c Catalin Popescu,^e Veaceslav Ursaki,^f Ion M. Tiginyanu,^f Daniel Errandonea^c and Francisco Javier Manjón^bReceived 30th June 2023,
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The effect of pressure on the structural, vibrational, and optical properties of lead thiogallate, PbGa₂S₄, crystallizing under room conditions in the orthorhombic EuGa₂S₄-type structure (space group *Fddd*), is investigated. The results from X-ray diffraction, Raman scattering, and optical-absorption measurements at a high pressure beyond 20 GPa are reported and compared not only to *ab initio* calculations, but also to the related compounds α'-Ga₂S₃, CdGa₂S₄, and HgGa₂S₄. Evidence of a partially reversible pressure-induced decomposition of PbGa₂S₄ into a mixture of Pb₆Ga₁₀S₂₁ and Ga₂S₃ above 15 GPa is reported. Thus, our measurements and calculations show a route for the high-pressure synthesis of Pb₆Ga₁₀S₂₁, which is isostructural to the stable Pb₆In₁₀S₂₁ compound at room pressure.

1 Introduction

Ternary metal chalcogenides of the A^{II}B₂X₄^{VI} family (X = S, Se, Te) can be basically divided into three subfamilies. The first one is constituted by compounds with both A and B cations showing a fourfold coordination. These compounds usually crystallize in the defect chalcopyrite, defect stannite (or defect famatinite), pseudo-cubic, and related structures that are derived from the zinc blende or wurtzite structures. Examples of those compounds are (Zn,Cd,Hg)(Al,Ga)₂(S,Se)₄ compounds. The second subfamily is constituted by compounds in which

there is a mixture of cations with fourfold and sixfold coordination. These compounds crystallize mainly in the spinel (MgAl₂O₄) or in related structures, such as (Mg,Zn,Cd,Mn)In₂(S,Se)₄, and show similar structural characteristics to many oxospinel. The third subfamily, and the less studied one, is composed of A cations featuring a coordination much larger than six. Examples of these compounds are those crystallizing in the orthorhombic EuGa₂S₄-type and related structures, such as (Ca,Sr,Pb,Eu,Sm,Yb)(Al,Ga,In)₂(S,Se,Te)₄.¹

The studies in the last subfamily of EuGa₂S₄-type compounds have come from the interest in the development first of phosphors,² and later of mid-infrared (35 μm) solid-state lasers,^{3–5} due to the large band gap, low-phonon energy, and chemical and thermal stability of these ternary sulphides. In particular, mid-infrared (mid-IR) laser radiation in PbGa₂S₄ has been consistently reported.^{6–10} This fact has resulted in recent studies to improve the crystal quality of this mid-IR laser material.^{11,12}

Several works have reported the structural, vibrational, and optical properties of PbGa₂S₄ under room conditions. From the structural point of view, PbGa₂S₄ is a layered material that crystallizes in the orthorhombic EuGa₂S₄-type structure (space group No. 70, *D*_{2h}²⁴-*Fddd*).^{2,13–15} The crystal structure (see Fig. 1 and Fig. S1 and S2 in the ESI†) is built on a framework of Ga₄ tetrahedral units and square antiprismatic PbS₈ polyhedra. The Ga₄ tetrahedra are located in layers stacked along the *c*-axis, where such layers are constructed from edge-shared Ga₂S₆ dimers connected to three other dimers *via* sharing corners. By contrast, the PbS₈ polyhedra are linked to two other

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15.3 GPa (shown in Fig. S7 in the ESI†) and those already described for PbGa₂S₄.

4 Conclusions

We have reported the effect of pressure on the structural, vibrational, and optical properties of lead thiogallate by means of powder HP-XRD, HP-RS, and HP-OA measurements beyond 20 GPa. Those measurements have been complemented with *ab initio* calculations at HP. First of all, we have checked that PbGa₂S₄ crystallizes at room conditions in the EuGa₂S₄-type orthorhombic (space group *Fddd*) structure by means of single-crystal XRD measurements. Then, we have shown by means of powder HP-XRD measurements that PbGa₂S₄ is an anisotropic material, as expected from its layered-like structure. Its axial and bulk moduli are of the same order as those of monoclinic α' -Ga₂S₃ and tetragonal CdGa₂S₄ and HgGa₂S₄; *i.e.* semiconductors with similar GaS₄ tetrahedra.

After checking the complex vibrational pattern of PbGa₂S₄ by means of polarized RS measurements at room conditions, we have shown that the vibrational modes of PbGa₂S₄ show phonon spectra that show a considerable similarity to those of α' -Ga₂S₃, CdGa₂S₄, and HgGa₂S₄. In fact, we have shown that the pressure dependence of the Raman-active modes in PbGa₂S₄ is similar to those of the mentioned semiconductors and have made a tentative assignment of the symmetry of the Raman-active modes experimentally observed.

Finally, we have measured the pressure dependence of the optical bandgap of PbGa₂S₄ by means of HP-OA measurements. We have confirmed that PbGa₂S₄ is an indirect bandgap semiconductor, whose bandgap decreases as pressure increases, unlike what happens in α' -Ga₂S₃, CdGa₂S₄, and HgGa₂S₄. The different behavior is explained by the contribution of the 6s lone electron pair of Pb to the topmost valence band and the strong decrease of the Pb–S bond distance upon compression that leads to a strong increase of the energy of the topmost valence band under pressure.

To finish, we want to stress that all our measurements have shown evidence of a partially reversible pressure-induced decomposition of PbGa₂S₄ into a mixture of Pb₆Ga₁₀S₂₁ and β' -Ga₂S₃ above 16 GPa. This decomposition is supported by enthalpy *vs.* pressure calculations of the three compounds and makes sense because both compounds show sixfold-coordinated Ga atoms in comparison with the fourfold-coordinated Ga atoms in PbGa₂S₄. The structure of the new compound Pb₆Ga₁₀S₂₁ at HP, which is isostructural to already known Pb₆In₁₀S₂₁ at RP, is reported at 23.5 GPa since it seems not to be stable at RP. Moreover, we have determined its Raman-active phonons and optical bandgap above 16 GPa. In summary, this work shows the first HP study of a compound with EuGa₂S₄-type (orthorhombic *Fddd*) structure and the route for the synthesis of Pb₆Ga₁₀S₂₁. Therefore, this work will be of interest for the study of the EuGa₂S₄-type subfamily of A^{II}B₂^{III}X₄^{VI} compounds, in which the effect of pressure is far from being understood.

Author contributions

Tania Garcia-Sanchez: investigation, formal analysis, discussion, writing, review and editing Samuel Gallego-Parra: investigation, formal analysis Akun Liang: investigation, formal analysis José Luis Rodrigo-Ramon: investigation, formal analysis Alfonso Muñoz: investigation, formal analysis Plácida Rodríguez-Hernandez: investigation, formal analysis Javier Gonzalez-Platas: investigation, formal analysis Juan Ángel Sans: investigation Vanesa Paula Cuenca-Gotor: investigation Hussien H. Osman: investigation Catalin Popescu: investigation Veaceslav Ursaki: investigation Ion M. Tiginyanu: investigation Daniel Errandonea: formal analysis, validation, funding acquisition, writing, review, and editing Francisco Javier Manjón: conceptualization, investigation, formal analysis, validation, writing, review, and editing, funding acquisition.

Conflicts of interest

There are no conflicts to declare.

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